

Origin of Improved Optical Quality of Monolayer Molybdenum Disulphide Grown on Hexagonal Boron Nitride Substrate

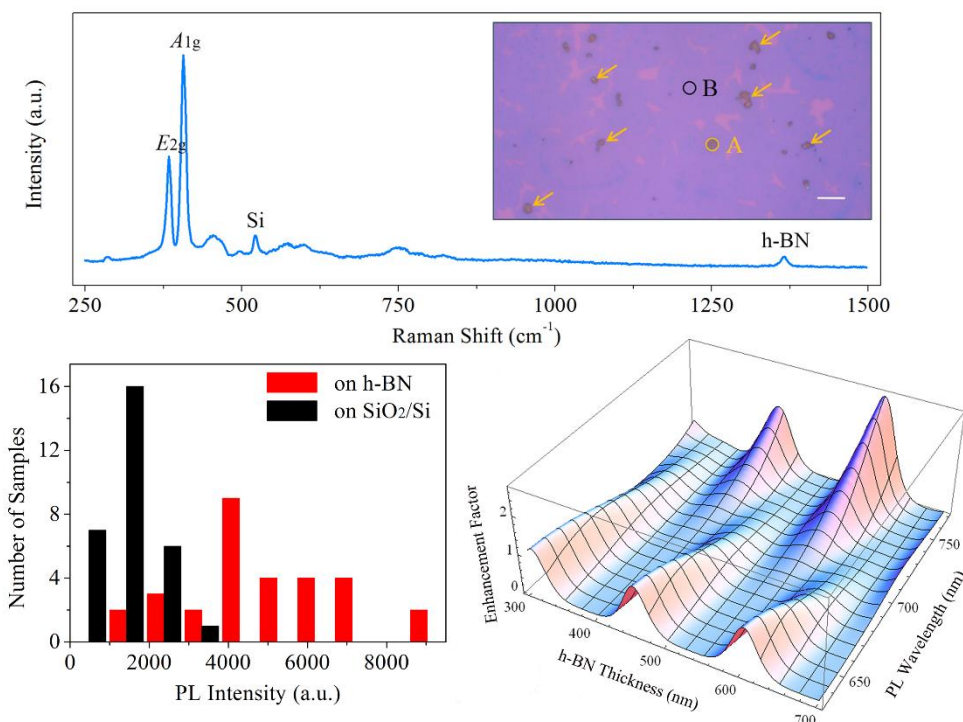
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We have devised and realized a high-yield and convenient method to synthesize monolayer MoS₂ directly on h-BN flakes via the chemical vapor deposition (CVD) method. Compared with that grown on SiO₂/Si substrate, the monolayer MoS₂ grown on h-BN exhibits enhanced photoluminescence (PL) and Raman signals as well as the smaller intensity ratio of E_{2g} to A_{1g}. Besides, its A_{1g} Raman mode exhibits clear stiffening, whereas its E_{2g} mode exhibits a negligible shift. We have calculated the PL intensity as function of both the h-BN thickness and the PL wavelength, based on light ray propagation in multilayer structure. Combining the theoretical and experimental analysis, we draw the conclusion that the enhanced PL and Raman signals of monolayer MoS₂ originates probably from the relatively weak doping effect from the h-BN substrate, rather than the optical interference effect suggested previously. Using h-BN as substrate may provide a possibility of investigating the intrinsic property of mono layer MoS₂, such as the novel valley-spin related property.

Figures



References

[1] Yi Wan, Hui Zhang, Wei Wang, Bowen Sheng, Kun Zhang, Yilun Wang, Qingjun Song, Nannan Mao, Yanping Li, Xinqiang Wang, Jin Zhang, and Lun Dai*, *Small* **12**, (2016) 198.